

**Silicon NPN Power Transistors****2SD536****DESCRIPTION**

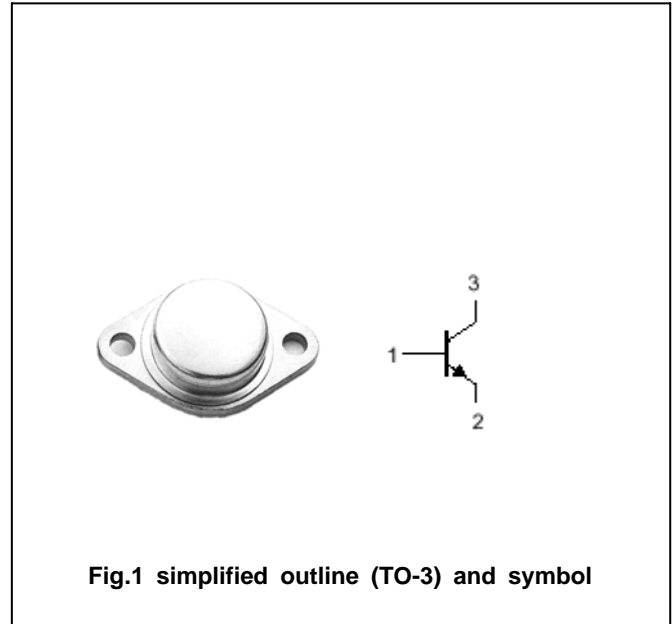
- With TO-3 package
- High voltage, high speed
- Low collector saturation voltage

**APPLICATIONS**

- Switching regulators
- DC-DC converters
- General purpose power amplifiers

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	200	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	200	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		10	A
I <sub>B</sub>	Base current		5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	100	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

**Silicon NPN Power Transistors****2SD536****CHARACTERISTICS**T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	200			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =0.1mA ; I <sub>E</sub> =0	200			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =0.1mA ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V ; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	50			

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PACKAGE OUTLINE

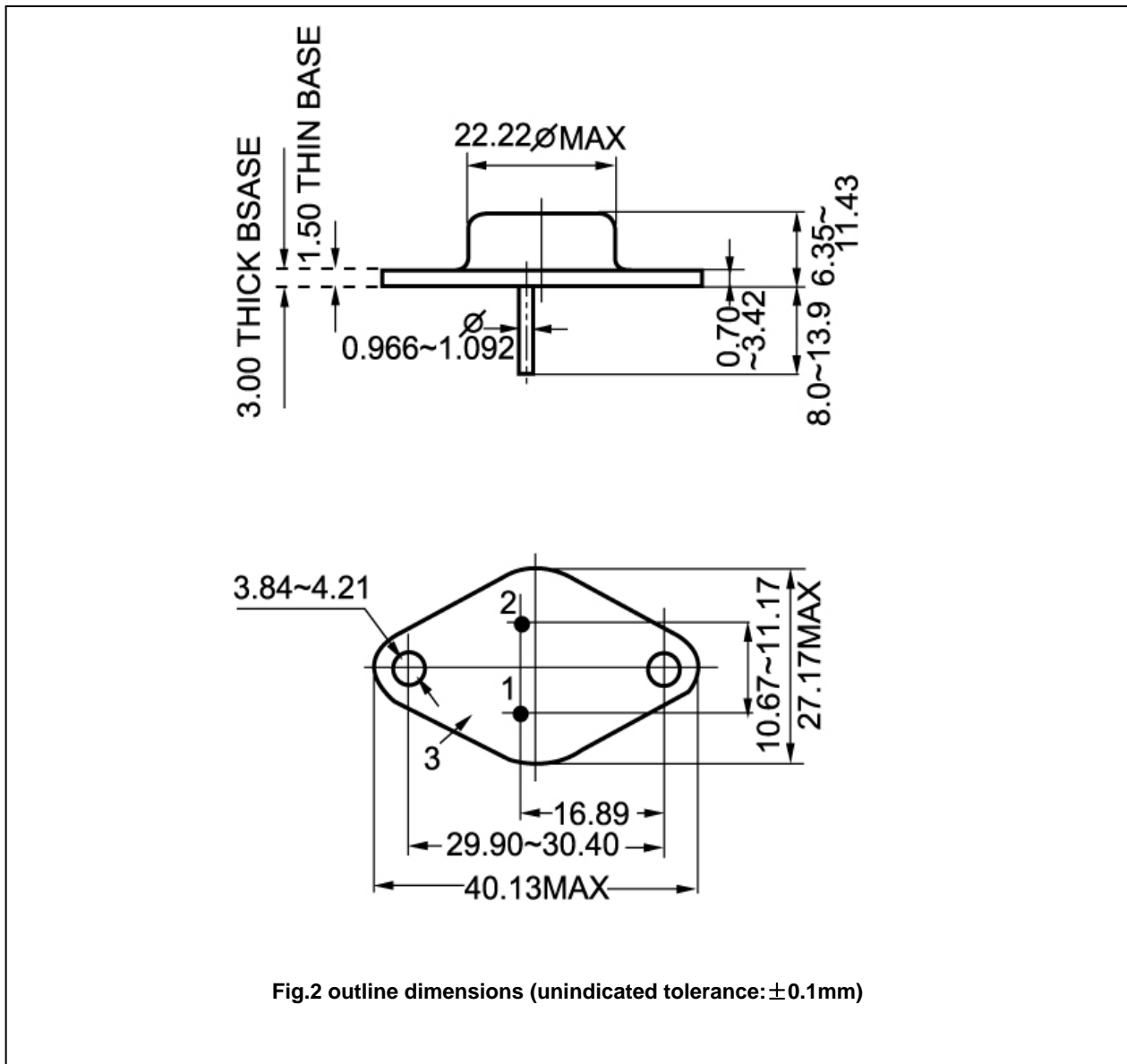


Fig.2 outline dimensions (unindicated tolerance: ±0.1mm)